

RESIDUE FREE OXIDE ETCH

ABSTRACT OF THE DISCLOSURE

A method for selectively etching silicon oxide is provided. A surface reaction phase is provided comprising flowing a surface reaction gas comprising hydrogen, nitrogen and fluorine containing components to form silicon oxide into a compound comprising silicon, hydrogen, nitrogen, and fluorine, forming the surface reaction gas into a plasma, and stopping the flow of the surface reaction gas. The surface is wet treated to remove the compound.

Fig. 1